



Dual P-Channel 30-V (D-S) MOSFET

| PRODUCT SUMMARY | | |
|-----------------|---------------------------|-----------|
| V_{DS} (V) | $r_{DS(on)}$ (Ω) | I_D (A) |
| -30 | 0.025 @ $V_{GS} = -10$ V | -7.1 |
| | 0.041 @ $V_{GS} = -4.5$ V | -5.5 |

FEATURES

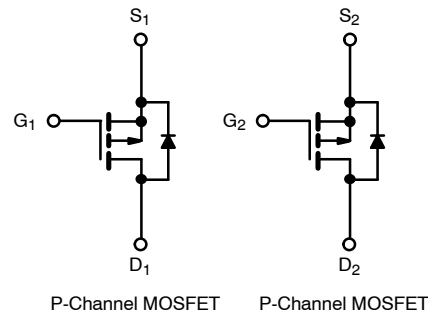
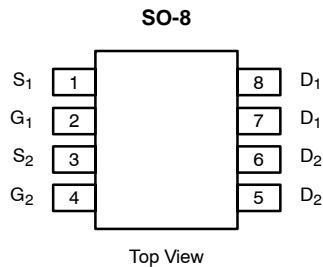
- TrenchFET® Power MOSFET
- Advanced High Cell Density Process



Pb-free
Available

APPLICATIONS

- Load Switches
 - Notebook PCs
 - Desktop PCs
 - Game Stations



Ordering Information: Si4925BDY
Si4925BDY—T1 (with Tape and Reel)
Si4925BDY—E3 (Lead (Pb)-Free)
Si4925BDY-T1—E3 (Lead (Pb)-Free) with Tape and Reel

| ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED) | | | | | |
|---|----------------|--------------------------|--------------|------------------|---|
| Parameter | Symbol | 10 secs | Steady State | Unit | |
| Drain-Source Voltage | V_{DS} | -30 | | V | |
| Gate-Source Voltage | V_{GS} | ± 20 | | | |
| Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a | I_D | $T_A = 25^\circ\text{C}$ | -7.1 | -5.3 | A |
| | | $T_A = 70^\circ\text{C}$ | -5.7 | -4.3 | |
| Pulsed Drain Current | I_{DM} | -40 | | | |
| continuous Source Current (Diode Conduction) ^a | I_S | -1.7 | -0.9 | | |
| Maximum Power Dissipation ^a | P_D | $T_A = 25^\circ\text{C}$ | 2.0 | 1.1 | W |
| | | $T_A = 70^\circ\text{C}$ | 1.3 | 0.7 | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | -55 to 150 | | $^\circ\text{C}$ | |

| THERMAL RESISTANCE RATINGS | | | | | |
|--|------------|-----------------|---------|------|--------------------|
| Parameter | Symbol | Typical | Maximum | Unit | |
| Maximum Junction-to-Ambient ^a | R_{thJA} | $t \leq 10$ sec | 50 | 62.5 | $^\circ\text{C/W}$ |
| | | Steady State | 85 | 110 | |
| Maximum Junction-to-Foot (Drain) | R_{thJF} | 30 | 40 | | |

Notes
a. Surface Mounted on 1" x 1" FR4 Board.

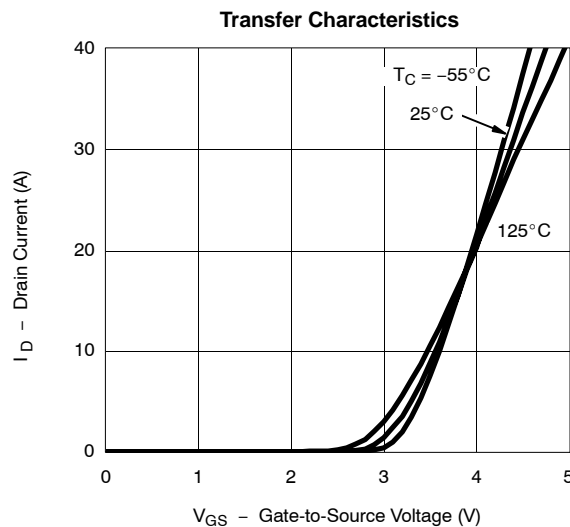
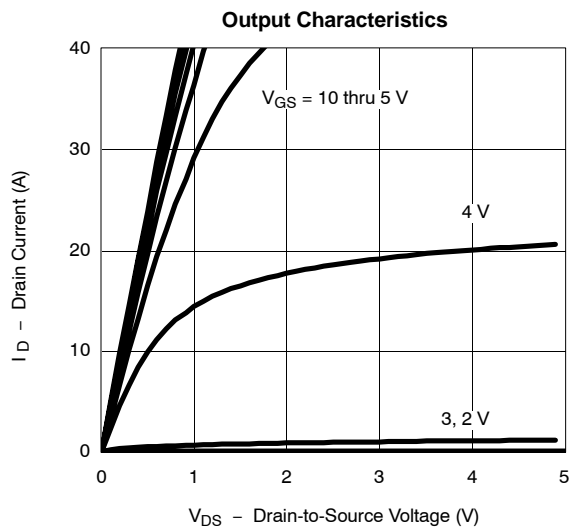
SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|---|---------------------|---|---|-------|-------|------|
| Static | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = -250 μA | -1 | | -3 | V |
| Gate-Body Leakage | I _{GSS} | V _{DS} = 0 V, V _{GS} = ±20 V | | | ±100 | nA |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = -30 V, V _{GS} = 0 V | | | -1 | μA |
| | | V _{DS} = -30 V, V _{GS} = 0 V, T _J = 55 °C | | | -25 | |
| On-State Drain Current ^a | I _{D(on)} | V _{DS} = -5 V, V _{GS} = -10 V | -40 | | | A |
| Drain-Source On-State Resistance ^a | r _{DS(on)} | V _{GS} = -10 V, I _D = -7.1 A | | 0.020 | 0.025 | Ω |
| | | V _{GS} = -4.5 V, I _D = -5.5 A | | 0.033 | 0.041 | |
| Forward Transconductance ^a | g _{fs} | V _{DS} = -10 V, I _D = -7.1 A | | 20 | | S |
| Diode Forward Voltage ^a | V _{SD} | I _S = -1.7 A, V _{GS} = 0 V | | -0.8 | -1.2 | V |
| Dynamic^b | | | | | | |
| Total Gate Charge | Q _g | V _{DS} = -15 V, V _{GS} = -10 V, I _D = -7.1 A | | 33 | 50 | nC |
| Gate-Source Charge | Q _{gs} | | | 5.4 | | |
| Gate-Drain Charge | Q _{gd} | | | 8.9 | | |
| Turn-On Delay Time | t _{d(on)} | V _{DD} = -15 V, R _L = 15 Ω I _D ≅ -1 A, V _{GEN} = -10 V, R _G = 6 Ω | | 9 | 15 | ns |
| Rise Time | t _r | | | 12 | 20 | |
| Turn-Off Delay Time | t _{d(off)} | | | 60 | 90 | |
| Fall Time | t _f | | | 34 | 50 | |
| Source-Drain Reverse Recovery Time | t _{rr} | | I _F = -1.7 A, di/dt = 100 A/μs | | 30 | |

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

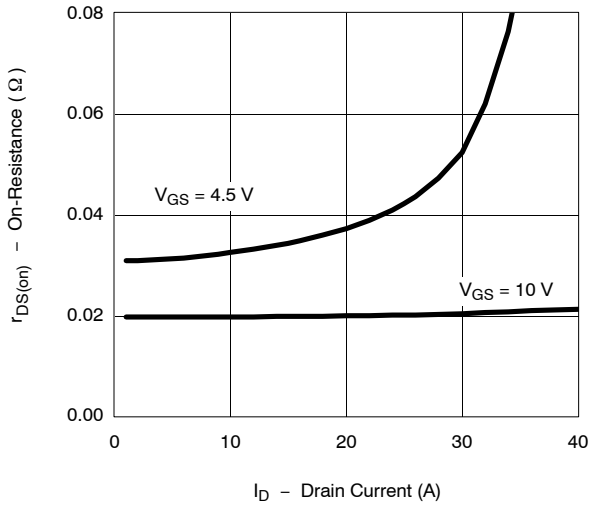
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

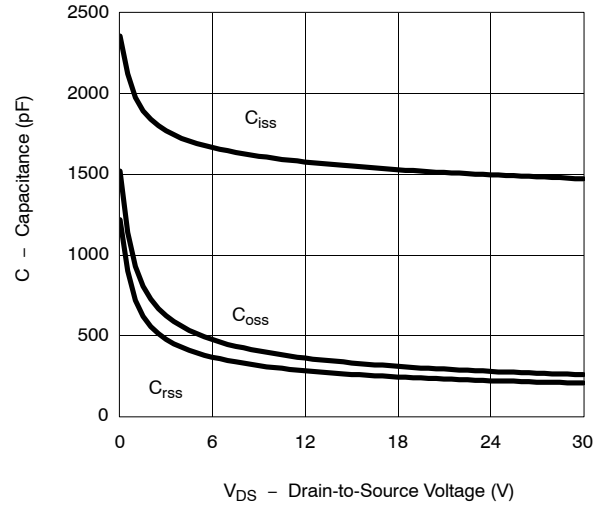


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

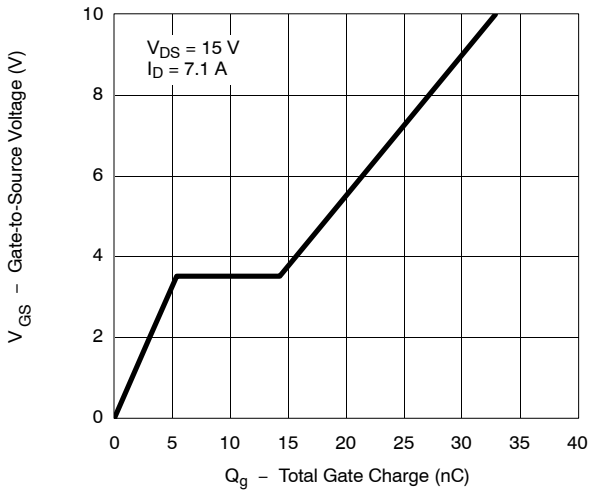
On-Resistance vs. Drain Current



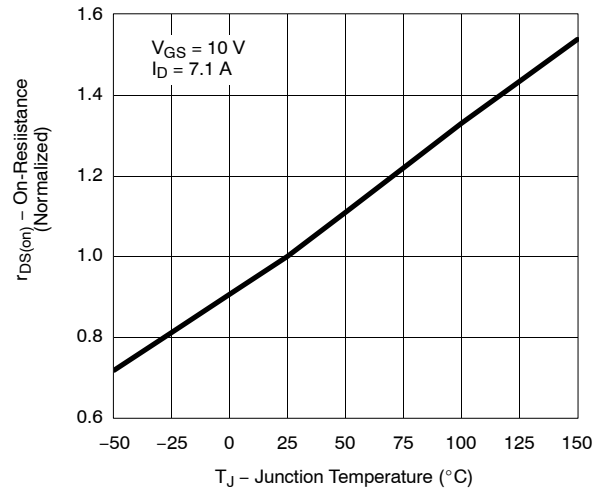
Capacitance



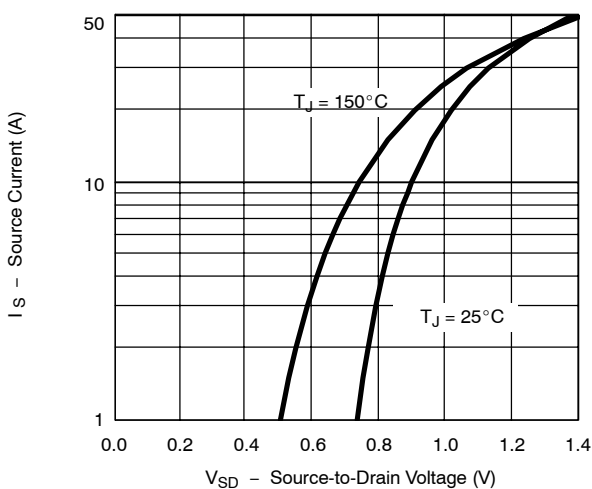
Gate Charge



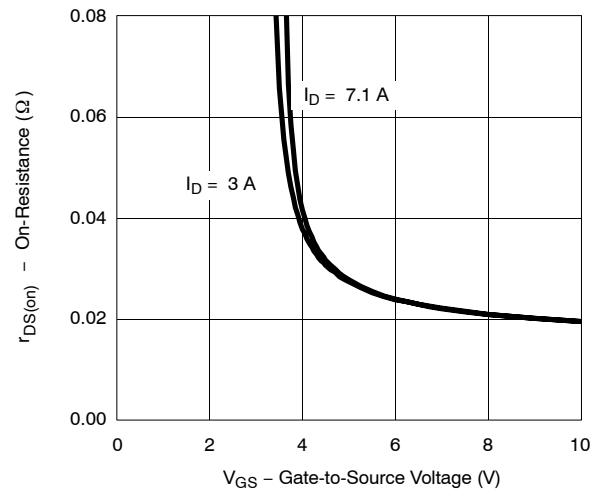
On-Resistance vs. Junction Temperature



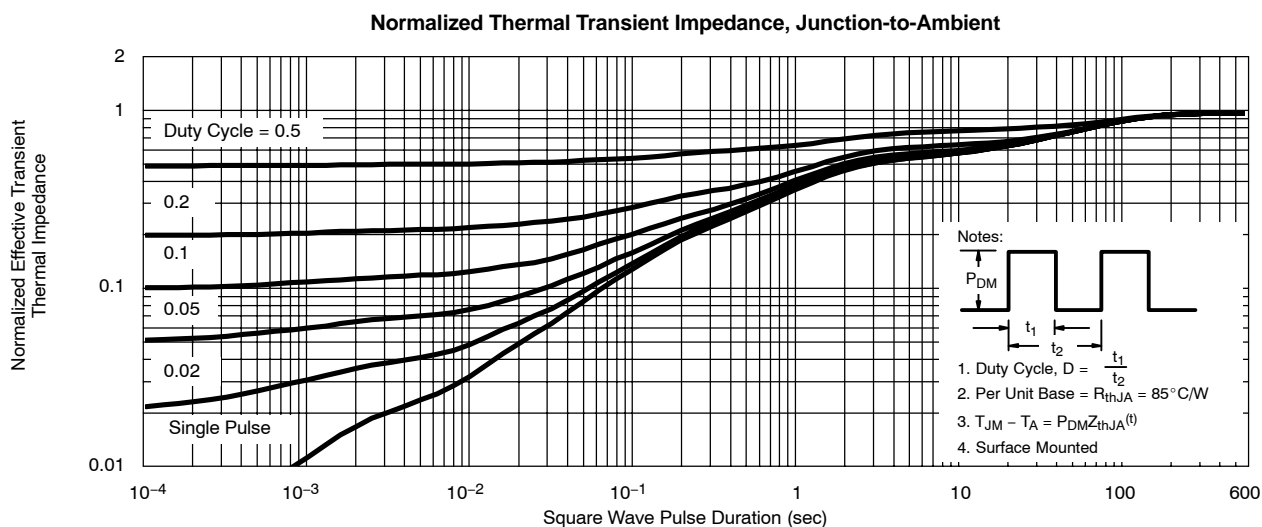
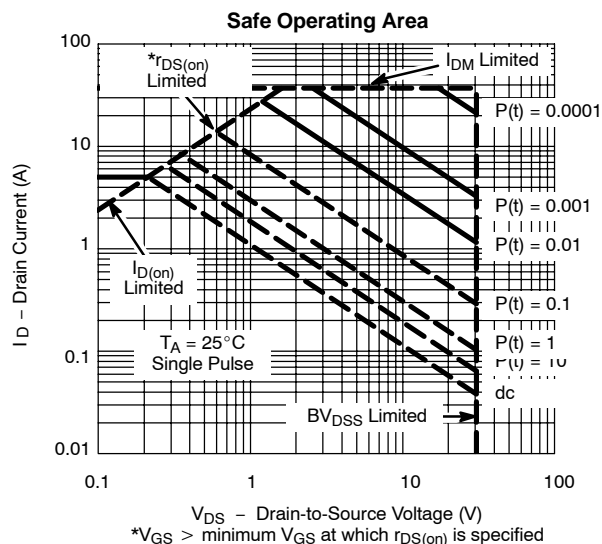
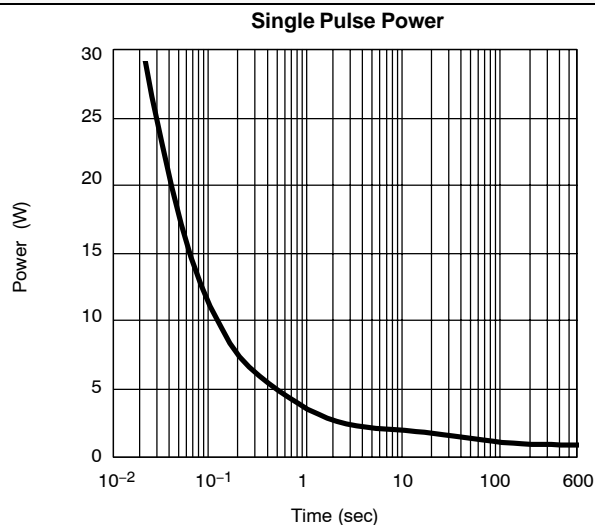
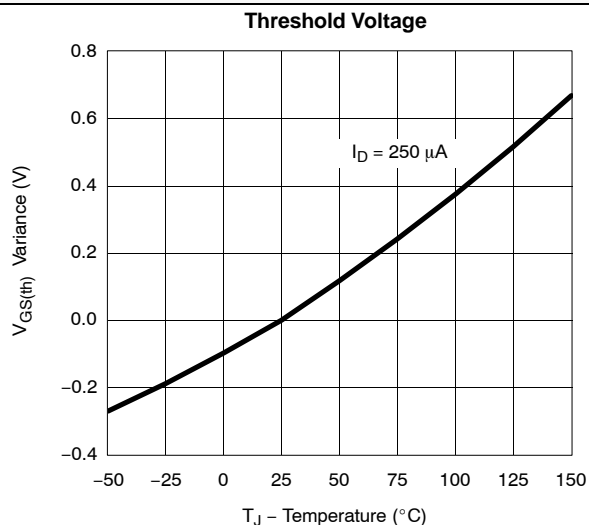
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

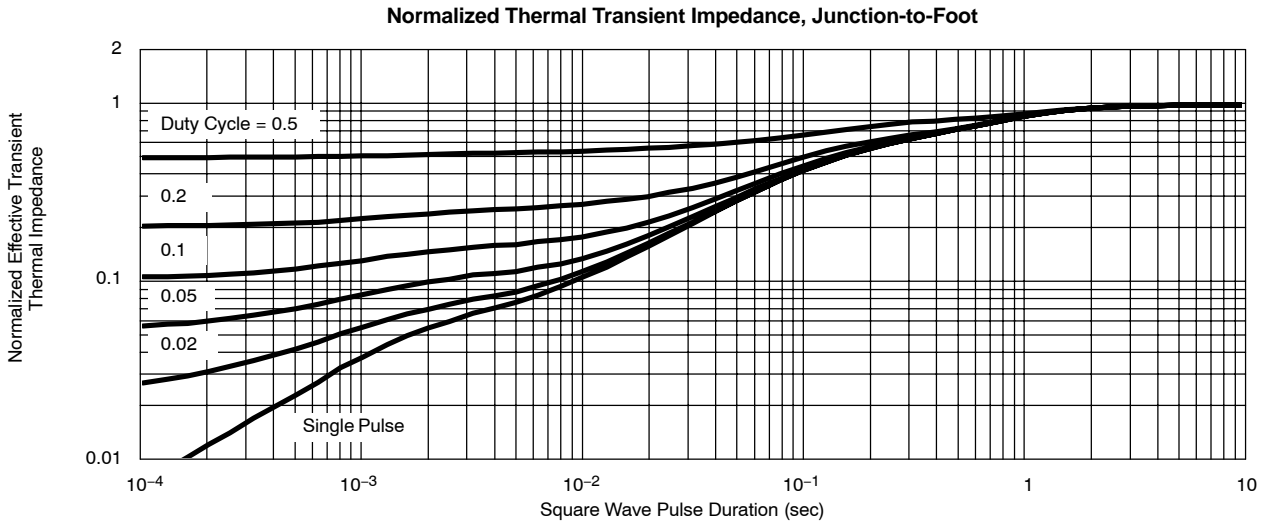


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)





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